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INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

(Chapter II of the Patent Cooperation Treaty)

(PCT Article 36 and Rule 70)

International application No. Inter		FOR FURTHER ACTION		See Form PCT/IPEA/416		
		International filing date 14.04.2004	(day/month/year)	Priority date (day/month/year) 16.04.2003		
	national I 5K3/12	Patent Class	sification (IPC) or na	tional classification and l	PC	- <u> </u>
٠.	licant TSUSH	ITA ELEC	CTRIC INDUST	RIAL CO., LTD.		
1.	Autnoi	ity under A	Article 35 and tran	ismitted to the applicar	it according to Artic	y this International Preliminary Examining le 36.
2.	This R	EPORT co	onsists of a total o	f 5 sheets, including t	nis cover sheet.	
3.	This re	port is also	o accompanied by	y ANNEXES, comprisi	ng:	
	a. 🛛			the International Bure		
		ana/o	s of the description r sheets containin nistrative instructi	ig rectifications authori	ngs which have bee zed by this Authorit	en amended and are the basis of this report y (see Rule 70.16 and Section 607 of the
		peyor	s which supersected the disclosure lemental Box.	le earlier sheets, but w In the international app	hich this Authority o lication as filed, as	considers contain an amendment that goes indicated in item 4 of Box No. I and the
	b. □	sequence	usuna ana⁄or tab	<i>ureau only)</i> a total of (in les related thereto, in c Listing (see Section 80	omnuter readable f	mber of electronic carrier(s)) , containing a orm only, as indicated in the Supplemental tive Instructions).
4.	This re	port conta	ins indications re	ating to the following it	ems:	
	⊠ Во	x No. I	Basis of the opin	nion		
	□ Во	x No. II	Priority			
	□ Во	x No. III	Non-establishme	ent of opinion with rega	rd to novelty, inven	tive step and industrial applicability
	□ Во	x No. IV	Lack of unity of i		,	are every and made man approaching
		x No. V	Reasoned states applicability; cita	ment under Article 35(2 tions and explanations	2) with regard to nov supporting such st	velty, inventive step or industrial atement
		x No. VI	Certain docume			
		x No. VII	Certain defects i	n the international app	lication	
	⊠ Bo	x No. VIII	Certain observa	tions on the internation	al application	
Date	of subm	ssion of the	demand		Date of completion	of this report
07.0	07.02.2005				17.08.2005	
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INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No. PCT/JP2004/005283

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	Box No. I Basis of the repo	ort				
1.	. With regard to the language , this report is based on the international application in the language filed, unless otherwise indicated under this item.					
	☐ This report is based on tr which is the language of	This report is based on translations from the original language into the following language, which is the language of a translation furnished for the purposes of:				
	publication of the inter	international search (under Rules 12.3 and 23.1(b)) publication of the international application (under Rule 12.4) international preliminary examination (under Rules 55.2 and/or 55.3)				
2.	With regard to the elements* of the international application, this report is based on <i>(replacement sheets whic</i> have been furnished to the receiving Office in response to an invitation under Article 14 are referred to in this report as "originally filed" and are not annexed to this report):					
	Description, Pages					
	1-78	as originally filed				
		•				
	Claims, Numbers					
	1-5, 7-17, 19-27	received on 21.07.2005				
	Drawings, Sheets					
	1/14-14/14	as originally filed				
	☐ a sequence listing and/or	r any related table(s) - see Supplemental Box Relating to Sequence Listing				
3.	☐ The amendments have r	The amendments have resulted in the cancellation of:				
	☐ the description, page	s				
	☐ the claims, Nos. ☐ the drawings, sheets/	fias				
	☐ the sequence listing ((specify):				
	Li any table(s) related to	o sequence listing (specify):				
4.	☐ This report has been established as if (some of) the amendments annexed to this report and listed below had not been made, since they have been considered to go beyond the disclosure as filed, as indicated in the Supplemental Box (Rule 70.2(c)).					
	☐ the description, page☐ the claims, Nos.	s				
	the drawings, sheets.	figs				
	☐ the sequence listing	(specify): o sequence listing (specify):				
	•					
	 * If item 4 applies, 	some or all of these sheets may be marked "superseded."				

INTERNATIONAL PRELIMINARY REPORT ON PATENTABILITY

International application No. PCT/JP2004/005283

Box No. V Reasoned statement under Article 35(2) with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

1. Statement

Novelty (N)

Yes: Claims

1-5,7-17,19-27

No: Claims

none

Inventive step (IS)

Yes: Claims

1-5,7-17,19-27

No: Claims

none

Industrial applicability (IA)

Yes: Claims

1-5,7-17,19-27

No: Claims none

2. Citations and explanations (Rule 70.7):

see separate sheet

Box No. VII Certain defects in the international application

The following defects in the form or contents of the international application have been noted:

see separate sheet

Box No. VIII Certain observations on the international application

The following observations on the clarity of the claims, description, and drawings or on the question whether the claims are fully supported by the description, are made:

see separate sheet

Re Item V

Reasoned statement with regard to novelty, inventive step or industrial applicability; citations and explanations supporting such statement

Reference is made to the following document/s/:

D1: US-B-6 306 2041 (LIN JOHN WEI-PING) 23 October 2001 (2001-10-23)

D2: PATENT ABSTRACTS OF JAPAN vol. 1998, no. 13, 30 November 1998 (1998-11-30) & JP 10 204350 A (SEIKO EPSON CORP), 4 August 1998 (1998-08-04)

D3: US 2002/151161 A1 (FURUSAWA MASAHIRO) 17 October 2002 (2002-10-17)

D4: EP-A-1 139 455 (SEIKO EPSON CORP) 4 October 2001 (2001-10-04)

1. Document D1 discloses (see e.g. col. 3, l. 28 - col. 4, l. 25) a discharging solution for forming patterns on a surface of a base, the solution comprising organic molecules having fluoroalkyl chains as a first pattern formation material, wherein the organic molecules contain a hydroxy group the surface tension of the solution being 0.45 mN/cm.

The subject matter of claim 1 differs from this known solution in that the organic molecules containing a hydroxy group are molecules of a straight chain.

The straight chain molecules containing a hydroxy group are more likely to form a self accumulated monomolecular layer on a substrate than the molecules which are not of a straight chain (i.e. the molecules known from document D1). Thus, the solution proposed in claim 1 forms more easily a water-repellent film on the surface of the substrate and undesired spreading of the discharged solution is prevented.

The other cited documents (D2-D4) all relate to methods of producing electronic devices but do not disclose a discharging solution having a surface tension of 0.2 mN/cm or more, in which organic molecules having fluoroalkyl chains are dissolved as a pattern formation material.

The subject matter of claim 1 appears, therefore, to involve an inventive step (Article 33(3) PCT).

2. Independent claim 12 is directed to a method of producing patterns, in which the inventive solution of claim 1 is used. Consequently the subject-matter of this claim also

seems new and inventive.

3. Claims 2 - 5, 7 -11, 13 - 17 and 19 - 27 which define preferred embodiments of the invention are dependent on claim 1 or claim 12, respectively, and as such also appear to meet the requirements of the PCT in respect of novelty and inventive step.

Re Item VII

Certain defects in the international application

- 1. Contrary to the requirements of Rule 5.1(a)(ii) PCT, the relevant background art disclosed in the documents D1 D4 is not mentioned in the description, nor are these documents identified therein (see also the Guidelines, paragraph 4.05).
- 2. The claims are not numbered consecutively (see Rule 6.1(b) PCT).

Re Item VIII

Certain observations on the international application

1. The word "similar" used in independent claim 26 has no well-recognised meaning and renders the definition of the subject-matter unclear (Guidelines, Chapter III-4.5). Using the expression "similar figure of geometry" does not overcome this deficiency.

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CLAIMS

1. (Amended) A discharging solution for forming patterns on a surface of a base, comprising organic molecules having fluoroalkyl chains as a first pattern formation material,

wherein the organic molecules are at least one selected from the group consisting of : organic molecules containing at least one group selected from a chlorosilyl group, an alkoxy group, a mercapto group, a hydroxy group, and an amino group; organic molecules of a straight chain containing a carboxy group or hydroxy group or an amino group; disulfide; silazane; and dithiol;

wherein the surface tension of the solution is 0.02 N/m (20 dyne/cm) or more.

- 2. The discharging solution according to claim 1, further comprising a second pattern formation material.
- 3. The discharging solution according to claim 2, wherein the second pattern formation material contains at least one kind of material selected from the group consisting of a precursor of a metal-oxide dielectric, a semiconductor, metal, and a polymer.
- 4. The discharging solution according to claim 3, wherein the second pattern formation material is the metal and the metal is a metal colloid.
- 5. The discharging solution according to claim 3, wherein the second pattern formation material is the polymer and the polymer is at least one kind selected from the group consisting of a conductive polymer, a semiconductor polymer, an insulting polymer, and a light-curable polymer.

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6. (Canceled)

7. The discharging solution according to claim 1, wherein the organic molecules are at least one selected from the group consisting of molecules represented by a composition formula: CF₃(CF₂)_nC₂H₄Si{(O·CH₂CH₂)_{m·OR¹}₃, and hydrolysate of the molecules, and}

in the composition formula, R^1 is a methyl group, an ethyl group, a propyl group, or a butyl group, and n and m are natural numbers of 1 to 10.

- 8. The discharging solution according to claim 3, wherein the second pattern formation material is the precursor of the metal-oxide dielectric and the precursor of the metal-oxide dielectric is at least one selected from the group consisting of metal alkoxide, metal acetylacetonate, metal carboxylate, and a metal inorganic compound.
- 9. The discharging solution according to claim 5, wherein the polymer is the semiconductor polymer and the semiconductor polymer is at least one selected from the group consisting of polyalkylthiophene and poly-9,9'dialkyl-fluorene-co-bithiophene.
- 10. The discharging solution according to claim 1, wherein a boiling point of a solvent contained in the solution is 80°C or higher.
- 25 11. The discharging solution according to claim 1, wherein the solution is applicable for forming patterns on a surface of a base by an ink-jet method.
 - 12. (Amended) A method for producing patterns comprising:

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discharging a solution having a surface tension of 0.02 N/m (20 dyne/cm) or more, in which organic molecules having fluoroalkyl chains are dissolved as a first pattern formation material, to a surface of a base by an ink-jet method to perform drawing; and

wherein the organic molecules are at least one selected from the group consisting of organic molecules containing at least one group selected from a chlorosilyl group, an alkoxy group, a mercapto group, a hydroxy group, and an amino group; organic molecules of a straight chain containing a carboxy group or hydroxy group or an amino group; disulfide; silazane; and dithiol;

evaporating a solvent contained in the discharged solution to form patterns containing the organic molecules.

- 13. The method for producing patterns according to claim 12, the solution further comprising a second pattern formation material, the method comprising evaporating a solvent contained in the discharged solution to form patterns containing the organic molecules and the second pattern formation material.
- 14. The method for producing patterns according to claim 13, comprising evaporating a solvent contained in the discharged solution to form patterns including a first pattern region containing a relatively large amount of the organic molecules and a second pattern region containing a relatively large amount of the second pattern formation material,

wherein the patterns are formed so that the first pattern region is present on the base side with respect to the second pattern region.

15. The method for producing patterns according to claim 13, wherein the second pattern formation material contains at least one kind of material

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selected from the group consisting of a precursor of a metal-oxide dielectric, a semiconductor, metal, and a polymer.

- 16. The method for producing patterns according to claim 15, wherein the second pattern formation material is the metal and the metal is a metal colloid.
 - 17. The method for producing patterns according to claim 15, wherein the second pattern formation material is the polymer and the polymer is at least one kind selected from the group consisting of a conductive polymer, a semiconductor polymer, an insulting polymer, and a light-curable polymer

18. (Canceld)

- 19. The method for producing patterns according to claim 12, wherein the organic molecules are at least one selected from the group consisting of molecules represented by a composition formula:
 - $CF_3(CF_2)_nC_2H_4Si\{(O-CH_2CH_2)_m-OR^1\}_3$, and hydrolyzate of the molecules, and in the composition formula, R^1 is a methyl group, an ethyl group, a propyl group, or a butyl group, and n and m are natural numbers of 1 to 10.
 - 20. The method for producing patterns according to claim 15, wherein the second pattern formation material is the precursor of the metal-oxide dielectric and the precursor of the metal-oxide dielectric is at least one selected from the group consisting of metal alkoxide, metal acetylacetonate, metal carboxylate, and a metal inorganic compound
 - 21. The method for producing patterns according to claim 17, wherein the

polymer is the semiconductor polymer and the semiconductor polymer is at least one selected from the group consisting of polyalkylthiophene and poly-9,9'dialkyl-fluorene-co-bithiophene

5 22. The method for producing patterns according to claim 12, wherein a boiling point of the solvent is 80°C or higher.

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- 23. The method for producing patterns according to claim 12, wherein, when the solution is discharged to the surface of the base, a surface temperature of the base is set to be lower by 5°C or more than a temperature of the solution to be discharged to the surface of the base.
- 24. A method for producing an electronic device comprising a method for producing patterns that includes:
- discharging a solution having a surface tension of 0.02 N/m (20 dyne/cm) or more, in which organic molecules having fluoroalkyl chains are dissolved as a first pattern formation material, to a surface of a base by an ink-jet method to perform drawing, the solution further containing a second pattern formation material; and
- evaporating a solvent contained in the discharged solution to form patterns containing the organic molecules and the second pattern formation material.
- 25. The method for producing an electronic device according to claim 24, wherein the second pattern formation material is at least one kind of material selected from the group consisting of a precursor of a metal-oxide dielectric, a semiconductor, metal, and a polymer, and

the electronic device is at least one selected from the group consisting

of metal wiring, an electrode, a transistor, a resistor, a capacitor, a microlens, and an imaging device.

26. (Amended) An electronic device comprising a base and patterns formed on a surface of the base,

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wherein the patterns include a first pattern region containing organic molecules having fluoroalkyl chains and a second pattern region containing at least one selected from metal, a semiconductor, a metal oxide, and a polymer,

the first pattern region and the second pattern region are stacked in this order on the surface of the base, and

a shape of the first pattern region is similar figure of geometry to a shape of the second pattern region.

27. The electronic device according to claim 26, wherein the first pattern
region is a monomolecular film of the organic molecules.